

Tomohisa Kato

List of Publications by Year in descending order

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147
papers

1,734
citations

430442

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148
all docs

148
docs citations

148
times ranked

673
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth of Shockley type stacking faults upon forward degradation in 4H-SiC p-n diodes. Journal of Applied Physics, 2016, 119, .	1.1	85
2	Short minority carrier lifetimes in highly nitrogen-doped 4H-SiC epilayers for suppression of the stacking fault formation in PiN diodes. Journal of Applied Physics, 2016, 120, .	1.1	80
3	Development of Ultrahigh-Voltage SiC Devices. IEEE Transactions on Electron Devices, 2015, 62, 396-404.	1.6	78
4	Correlation between reliability of thermal oxides and dislocations in n-type 4H-SiC epitaxial wafers. Applied Physics Letters, 2006, 89, 022909.	1.5	70
5	Growth rate and surface morphology of 4H-SiC crystals grown from Si-Cr-C and Si-Cr-Al-C solutions under various temperature gradient conditions. Journal of Crystal Growth, 2014, 401, 681-685.	0.7	58
6	Entropy change in lithium ion cells on charge and discharge. Journal of Applied Electrochemistry, 2002, 32, 251-258.	1.5	55
7	Injected carrier concentration dependence of the expansion of single Shockley-type stacking faults in 4H-SiC PiN diodes. Journal of Applied Physics, 2018, 123, .	1.1	48
8	Effect of aluminum addition on the surface step morphology of 4H-SiC grown from Si-Cr-C solution. Journal of Crystal Growth, 2015, 423, 45-49.	0.7	45
9	The growth of low resistivity, heavily Al-doped 4H-SiC thick epilayers by hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 380, 85-92.	0.7	34
10	Raman characterization of damaged layers of 4H-SiC induced by scratching. AIP Advances, 2016, 6, .	0.6	30
11	High Throughput SiC Wafer Polishing with Good Surface Morphology. Materials Science Forum, 2007, 556-557, 753-756.	0.3	28
12	Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-n diodes. Japanese Journal of Applied Physics, 2018, 57, 04FR07.	0.8	28
13	Temperature-Dependent Behavior of 4H-Silicon Carbide Surface Morphology Etched Using Chlorine Trifluoride Gas. Journal of the Electrochemical Society, 2009, 156, H971.	1.3	27
14	Dependences of contraction/expansion of stacking faults on temperature and current density in 4H-SiC p-n diodes. Japanese Journal of Applied Physics, 2018, 57, 061301.	0.8	27
15	Determination of carrier concentration by Fano interference of Raman scattering in heavily doped n-type 4H-SiC. Journal of Applied Physics, 2012, 112, .	1.1	26
16	Determination of Etch Rate Behavior of 4H-SiC Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2007, 46, 7875.	0.8	24
17	Characterization of Electric Discharge Machining for Silicon Carbide Single Crystal. Materials Science Forum, 0, 600-603, 855-858.	0.3	24
18	Micro-structural analysis of local damage introduced in subsurface regions of 4H-SiC wafers during chemo-mechanical polishing. Journal of Applied Physics, 2016, 119, .	1.1	22

#	ARTICLE	IF	CITATIONS
19	Challenges of High-Performance and High-Reliability in SiC MOS Structures. Materials Science Forum, 0, 717-720, 703-708.	0.3	21
20	Structural analysis of double-layer Shockley stacking faults formed in heavily-nitrogen-doped 4H-SiC during annealing. Journal of Applied Physics, 2017, 122, .	1.1	21
21	Modification of the surface morphology of 4H-SiC by addition of Sn and Al in solution growth with SiCr solvents. Journal of Crystal Growth, 2017, 458, 37-43.	0.7	21
22	The photoelastic constant and internal stress around micropipe defects of 6H-SiC single crystal. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 57, 147-149.	1.7	20
23	Flux-Controlled Sublimation Growth by an Inner Guide-Tube. Materials Science Forum, 2002, 389-393, 83-86.	0.3	20
24	Effects of Dislocations on Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. Materials Science Forum, 2005, 483-485, 661-664.	0.3	20
25	Determination of free carrier density in the low doping regime of 4H-SiC by Raman scattering. Applied Physics Letters, 2008, 93, .	1.5	20
26	Growth of P-type 4H-SiC single crystals by physical vapor transport using aluminum and nitrogen co-doping. Journal of Crystal Growth, 2017, 470, 154-158.	0.7	20
27	Defect and Growth Analysis of SiC Bulk Single Crystals with High Nitrogen Doping. Materials Science Forum, 2007, 556-557, 239-242.	0.3	19
28	Growth Rate and Surface Morphology of 4H-SiC Single Crystal Grown under Various Supersaturations Using Si-C Solution. Materials Science Forum, 0, 740-742, 23-26.	0.3	19
29	Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing. Materials Science Forum, 0, 778-780, 370-373.	0.3	19
30	Quantitative Analysis of Nanoscale Step Dynamics in High-Temperature Solution-Grown Single Crystal 4H-SiC via In Situ Confocal Laser Scanning Microscope. Crystal Growth and Design, 2017, 17, 2844-2851.	1.4	19
31	In-situ observation of silicon carbide sublimation growth by X-ray topography. Journal of Crystal Growth, 2001, 222, 579-585.	0.7	17
32	Origin analysis of expanded stacking faults by applying forward current to 4H-SiC p-n diodes. Applied Physics Express, 2017, 10, 081201.	1.1	17
33	Control of temperature distribution to suppress macro-defects in solution growth of 4H-SiC crystals. Journal of Crystal Growth, 2019, 523, 125151.	0.7	16
34	Relationship between depth of basal-plane dislocations and expanded stacking faults by application of forward current to 4H-SiC p-i-n diodes. Applied Physics Express, 2019, 12, 051007.	1.1	16
35	High-Quality SiC Bulk Single Crystal Growth Based on Simulation and Experiment. Materials Science Forum, 2004, 457-460, 29-34.	0.3	15
36	Cutting Speed of Electric Discharge Machining for SiC Ingot. Materials Science Forum, 0, 717-720, 861-864.	0.3	15

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37	Local Strain Distribution and Microstructure of Grinding-Induced Damage Layers in SiC Wafer. Journal of Electronic Materials, 2018, 47, 6722-6730.	1.0	15
38	Reducing Stacking Faults in Highly Doped N-Type 4H-SiC Crystal. Materials Science Forum, 0, 679-680, 8-11.	0.3	14
39	Observation of double Shockley stacking fault expansion in heavily-nitrogen-doped 4H-SiC using PL technique. Journal of Crystal Growth, 2017, 468, 889-893.	0.7	14
40	Transition of conduction mechanism from band to variable-range hopping conduction due to Al doping in heavily Al-doped 4H-SiC epilayers. Japanese Journal of Applied Physics, 2019, 58, 098004.	0.8	14
41	Reduction of threading screw dislocations in 4H-SiC crystals by a hybrid method with solution growth and physical vapor transport growth. Journal of Crystal Growth, 2021, 568-569, 126189.	0.7	14
42	Dynamic characteristics of large current capacity module using 16-kV ultrahigh voltage SiC flip-type n-channel IE-IGBT. , 2014, , .		13
43	Reliability of Gate Oxides on 4H-SiC Epitaxial Surface Planarized by CMP Treatment. Materials Science Forum, 0, 778-780, 545-548.	0.3	12
44	4H-SiC Growth from Si-Cr-C Solution under Al and N Co-Doping Conditions. Materials Science Forum, 0, 821-823, 9-13.	0.3	12
45	Dependence of conduction mechanisms in heavily Al-doped 4H-SiC epilayers on Al concentration. Applied Physics Express, 2018, 11, 101302.	1.1	12
46	Deep Ultraviolet Raman Microspectroscopic Characterization of Polishing-Induced Surface Damage in SiC Crystals. Journal of the Electrochemical Society, 2006, 153, G319.	1.3	11
47	Expansion and contraction of single Shockley stacking faults in SiC epitaxial layer under ultraviolet irradiation. Applied Physics Express, 2019, 12, 041006.	1.1	11
48	Electric Discharge Machining for Silicon Carbide and Related Materials. Materials Science Forum, 0, 600-603, 851-854.	0.3	10
49	4H Silicon Carbide Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 600-603, 655-658.	0.3	10
50	Evaluation of the increase in threading dislocation during the initial stage of physical vapor transport growth of 4H-SiC. Japanese Journal of Applied Physics, 2018, 57, 065501.	0.8	10
51	SiC Single Crystal Growth Rate Measurement by In-Situ Observation using the Transmission X-Ray Technique. Materials Science Forum, 2000, 338-342, 75-78.	0.3	9
52	Observation of surface polarity dependent phonons in SiC by deep ultraviolet Raman spectroscopy. Physical Review B, 2007, 75, .	1.1	9
53	4H-SiC Surface Morphology Etched Using ClF ₃ Gas. Materials Science Forum, 2010, 645-648, 787-790.	0.3	9
54	Difference of double Shockley-type stacking faults expansion in highly nitrogen-doped and nitrogen-boron co-doped n-type 4H-SiC crystals. Journal of Crystal Growth, 2017, 468, 879-882.	0.7	9

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55	Characterization of double Shockley-type stacking faults formed in lightly doped 4H-SiC epitaxial films. Journal of Crystal Growth, 2018, 490, 89-96.	0.7	9
56	In situ x-ray topography of silicon carbide during crystal growth by sublimation method. Review of Scientific Instruments, 2000, 71, 2829-2832.	0.6	8
57	Investigation of In-Grown Dislocations in 4H-SiC Epitaxial Layers. Materials Science Forum, 2006, 527-529, 147-152.	0.3	8
58	Effect of heat transfer on macroscopic and microscopic crystal quality in silicon carbide sublimation growth. Journal of Crystal Growth, 2007, 303, 342-344.	0.7	8
59	Etching Rate Behavior of 4H-Silicon Carbide Using Chlorine Trifluoride Gas. ECS Transactions, 2008, 13, 39-52.	0.3	8
60	High-Speed Slicing of SiC Ingot by High-Speed Multi Wire Saw. Materials Science Forum, 2014, 778-780, 771-775.	0.3	8
61	Growth of Low Resistivity n-Type 4H-SiC Bulk Crystals by Sublimation Method Using Co-Doping Technique. Materials Science Forum, 2014, 778-780, 47-50.	0.3	8
62	Change in Surface Morphology by Addition of Impurity Elements in 4H-SiC Solution Growth with Si Solvent. Materials Science Forum, 0, 821-823, 14-17.	0.3	8
63	Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher. Materials Science Forum, 0, 821-823, 553-556.	0.3	8
64	Growth of Low Resistivity p-Type 4H-SiC Crystals by Sublimation with Using Aluminum and Nitrogen Co-Doping. Materials Science Forum, 0, 858, 77-80.	0.3	8
65	Effects of Al addition to Si-based flux on the growth of 4H-SiC films by vapourâ€“liquidâ€“solid pulsed laser deposition. CrystEngComm, 2017, 19, 5188-5193.	1.3	8
66	Comparison of Conduction Mechanisms in Heavily Al-Doped 4H-SiC and Heavily Al- and N-Codoped 4H-SiC. Materials Science Forum, 0, 924, 188-191.	0.3	8
67	Nondestructive measurements of depth distribution of carrier lifetimes in 4H-SiC thick epitaxial layers using time-resolved free carrier absorption with intersectional lights. Review of Scientific Instruments, 2020, 91, 123902.	0.6	8
68	Dislocation constraint by etch back process of seed crystal in the SiC sublimation growth. Journal of Crystal Growth, 2001, 233, 219-225.	0.7	7
69	Numerical Simulation of Heat and Mass Transfer in SiC Sublimation Growth. Materials Science Forum, 2002, 389-393, 43-46.	0.3	7
70	Large Diameter and Long Length Growth of SiC Single Crystal. Materials Science Forum, 2004, 457-460, 99-102.	0.3	7
71	Demonstration of motor drive with SiC normally-off IBMOSFET/SBD power converter. , 2007, , .		7
72	Morphology Improvement of Step Bunching on 4H-SiC Wafers by Polishing Technique. Materials Science Forum, 0, 645-648, 763-765.	0.3	7

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73	Enlargement Growth of Large 4H-SiC Bulk Single Crystal. Materials Science Forum, 0, 679-680, 3-7.	0.3	7
74	Density of Etch Pits on C-Face 4H-SiC Surface Produced by ClF_3 Gas. Materials Science Forum, 0, 725, 49-52.	0.3	7
75	Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 778-780, 738-741.	0.3	7
76	Growth Study of p-Type 4H-SiC with Using Aluminum and Nitrogen Co-Doping by 2-Zone Heating Sublimation Method. Materials Science Forum, 0, 821-823, 47-50.	0.3	7
77	Mirror Etching of Single Crystalline C-Face 4H-Silicon Carbide Wafer by Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2017, 6, P582-P585.	0.9	7
78	Glide velocities of Si-core partial dislocations for double-Shockley stacking fault expansion in heavily nitrogen-doped SiC during high-temperature annealing. Journal of Applied Physics, 2018, 124, .	1.1	7
79	Application of Defect Conversion Layer by Solution Growth for Reduction of TSDs in 4H-SiC Bulk Crystals by PVT Growth. Materials Science Forum, 0, 963, 71-74.	0.3	7
80	Initiation of Shockley Stacking Fault Expansion in 4H-SiC Pi-N Diodes. Materials Science Forum, 0, 963, 280-283.	0.3	7
81	Structural analysis of interfacial dislocations and expanded single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-i-n diodes. Japanese Journal of Applied Physics, 2019, 58, 011005.	0.8	7
82	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. Journal of Applied Physics, 2020, 128, 105702.	1.1	7
83	Massive reduction of threading screw dislocations in 4H-SiC crystals grown by a hybrid method combined with solution growth and physical vapor transport growth on higher off-angle substrates. Applied Physics Express, 2021, 14, 085506.	1.1	7
84	Stress Analysis of SiC Bulk Single Crystal Growth by Sublimation Method. Materials Science Forum, 2003, 433-436, 13-16.	0.3	6
85	Electric Discharge Machining for Silicon Carbide in Gases of Ar, Ar-CH_4 and Ar-CF_4 Mixtures. Materials Science Forum, 0, 645-648, 869-872.	0.3	6
86	Control of Void Formation in 4H-SiC Solution Growth. Materials Science Forum, 0, 717-720, 57-60.	0.3	6
87	Density and Behavior of Etch Pits on C-Face 4H-SiC Surface Produced by ClF_3 Gas. Materials Science Forum, 2012, 717-720, 379-382.	0.3	6
88	High-Throughput Screening of Si-Ni Flux for SiC Solution Growth Using a High-Temperature Laser Microscope Observation and Secondary Ion Mass Spectroscopy Depth Profiling. ACS Combinatorial Science, 2013, 15, 287-290.	3.8	6
89	13-kV, 20-A 4H-SiC PiN Diodes for Power System Applications. Materials Science Forum, 2014, 778-780, 855-858.	0.3	6
90	Uniform growth of SiC single crystal thin films via a metal-Si alloy flux by vapour-liquid-solid pulsed laser deposition: the possible existence of a precursor liquid flux film. CrystEngComm, 2016, 18, 143-148.	1.3	6

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91	Temperature dependence of double Shockley stacking fault behavior in nitrogen-doped 4H-SiC studied by in-situ synchrotron X-ray topography. <i>Acta Materialia</i> , 2020, 194, 387-393.	3.8	6
92	Spectroscopic Measurement of Electric Discharge Machining for Silicon Carbide. <i>Materials Science Forum</i> , 2009, 615-617, 609-612.	0.3	5
93	AlN bulk crystal growth by sublimation method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1775-1777.	0.8	5
94	Thermoelectric Properties of Single-Crystalline SiC and Dense Sintered SiC for Self-Cooling Devices. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 031301.	0.8	5
95	Slicing of Rotating SiC Ingot by Electric Discharge Machining. <i>Materials Science Forum</i> , 0, 740-742, 843-846.	0.3	5
96	Morphological stability of 4H-SiC crystals in solution growth on {0001} and {111} surfaces. <i>Journal of Crystal Growth</i> , 2017, 468, 883-888.	0.7	5
97	Relationship between Temperature Dependencies of Resistivity and Hall Coefficient in Heavily Al-Doped 4H-SiC Epilayers. <i>Materials Science Forum</i> , 0, 963, 324-327.	0.3	5
98	Development of New Complex Machining Technology for Single Crystal Silicon Carbide Polishing. <i>International Journal of Automation Technology</i> , 2016, 10, 786-793.	0.5	5
99	Direct visualization of kinetic reversibility of crystallization and dissolution behavior at solution growth interface of SiC in Si-Cr solvent. <i>Surfaces and Interfaces</i> , 2022, 28, 101664.	1.5	5
100	In-situ Observation of SiC Bulk Single Crystal Growth by X-Ray Topography. <i>Materials Science Forum</i> , 2000, 338-342, 457-460.	0.3	4
101	Growth and Evaluation of High Quality SiC Crystal by Sublimation Method. <i>Materials Science Forum</i> , 2002, 389-393, 87-90.	0.3	4
102	Development of Large SiC Wafer Processing Technique in "Novel Semiconductor Power Electronics Project Realizing Low Carbon Emission Society"; Supported by NEDO. <i>Journal of the Japan Society for Precision Engineering</i> , 2014, 80, 18-22.	0.0	4
103	Development of Multi-Wire Electric Discharge Machining for SiC Wafer Processing. <i>Materials Science Forum</i> , 0, 778-780, 776-779.	0.3	4
104	Effect of Forced Convection by Crucible Design in Solution Growth of SiC Single Crystal. <i>Materials Science Forum</i> , 0, 821-823, 22-25.	0.3	4
105	Formation and Removal of Carbon Film on Silicon Carbide Surface Using Chlorine Trifluoride Gas. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P441-P445.	0.9	4
106	Characterization of stacking faults with emission wavelengths of over 500 nm formed in 4H-SiC epitaxial films. <i>Journal of Crystal Growth</i> , 2017, 476, 99-106.	0.7	4
107	Crystal growth and evaluation of nitrogen and aluminum co-doped N-type 4H-SiC grown by physical vapor transport. <i>Journal of Crystal Growth</i> , 2018, 498, 224-229.	0.7	4
108	Influence of Additives on Surface Smoothness and Polytype Stability in Solution Growth of n-Type 4H-SiC. <i>Materials Science Forum</i> , 0, 924, 55-59.	0.3	4

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109	Observation of multilayer Shockley-type stacking fault formation during process of epitaxial growth on highly nitrogen-doped 4H-SiC substrate. Japanese Journal of Applied Physics, 2019, 58, 021001.	0.8	4
110	Anomalous Temperature Dependence of the Hall Coefficient of Heavily Al-Doped 4H-SiC Epilayers in the Band Conduction Region. Materials Science Forum, 0, 1004, 215-223.	0.3	4
111	Sign of Hall coefficient in nearest-neighbor hopping conduction in heavily Al-doped p-type 4H-SiC. Japanese Journal of Applied Physics, 2020, 59, 051004.	0.8	4
112	Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. Materials Science Forum, 2014, 778-780, 151-154.	0.3	3
113	Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher. Materials Science Forum, 0, 963, 520-524.	0.3	3
114	Platinum additive impacts on vapor-liquid-solid growth chemical interface for high-quality SiC single crystal films. Materials Today Chemistry, 2020, 16, 100266.	1.7	3
115	Simple physical model for the sign of the Hall coefficient in variable-range hopping conduction in heavily Al-doped p-type 4H-SiC. Japanese Journal of Applied Physics, 2021, 60, 031008.	0.8	3
116	Characterization of Inclusions in SiC Bulk Crystals Grown by Modified Lely Method. Materials Science Forum, 2002, 389-393, 75-78.	0.3	2
117	AlN bulk single crystal growth on SiC and AlN substrates by sublimation method. , 2010, , .		2
118	Etch Pits on 4H-SiC Surface Produced by ClF ₃ Gas. Materials Science Forum, 0, 679-680, 286-289.	0.3	2
119	Growth of 4H-SiC in Current-Controlled Liquid Phase Epitaxy. Materials Science Forum, 2013, 740-742, 3-6.	0.3	2
120	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2013, 2, N3025-N3027.	0.9	2
121	Ultrahigh voltage SiC bipolar devices. , 2013, , .		2
122	Development of ultrahigh voltage SiC power devices. , 2014, , .		2
123	Effects of Machining Fluid on Electric Discharge Machining of SiC Ingot. Materials Science Forum, 2014, 778-780, 767-770.	0.3	2
124	Effect of Al addition to Si-Ni flux on pulsed laser deposition of SiC thin films. Journal of the Ceramic Society of Japan, 2016, 124, 506-509.	0.5	2
125	Immobilization Phenomenon of Partials Surrounding Double Shockley Stacking Faults in Heavily Nitrogen Doped 4H-SiC Crystal with Thermal Anneal. Materials Science Forum, 0, 924, 160-163.	0.3	2
126	Etching Rate Profile of C-Face 4H-SiC Wafer Depending on Total Gas Flow Rate of Chlorine Trifluoride and Nitrogen. Materials Science Forum, 0, 1004, 173-179.	0.3	2

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127	Anomalous Conduction between the Band and Nearest-Neighbor Hopping Conduction Regions in Heavily Al-Doped p-Type 4H-SiC. Materials Science Forum, 0, 1004, 224-230.	0.3	2
128	Immobilization of partial dislocations bounding double Shockley stacking faults in 4H-SiC observed by in situ synchrotron X-ray topography. Materialia, 2021, 20, 101246.	1.3	2
129	Comparative Study of Performance of SiC SJ-MOSFETs Formed by Multi-epitaxial Growth and Trench-filling Epitaxial Growth. , 2022, , .		2
130	X-ray Topographic Study of SiC Crystal at High Temperature. Materials Science Forum, 2000, 338-342, 461-464.	0.3	1
131	Dislocation Constraint by Etch-Back Process of Seed Crystal in SiC Bulk Crystal Growth. Materials Science Forum, 2002, 389-393, 111-114.	0.3	1
132	Effect of Radiation in Solid during SiC Sublimation Growth. Materials Research Society Symposia Proceedings, 2006, 911, 2.	0.1	1
133	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGaN/GaN HFET. Materials Science Forum, 2007, 556-557, 1043-1046.	0.3	1
134	Transport parameters of single crystalline SiC for self-cooling device. , 2007, , .		1
135	4H-Silicon Carbide Wafer Surface after Chlorine Trifluoride Gas Etching. Materials Science Forum, 0, 924, 369-372.	0.3	1
136	Non-Plasma Dry Etcher Design for 200 mm-Diameter Silicon Carbide Wafer. Materials Science Forum, 0, 1004, 167-172.	0.3	1
137	Vapor-liquid-solid growth of 4H-SiC single crystal films with extremely low carrier densities in chemical vapor deposition with a Pt-Si alloy flux and X-ray topography analysis of their dislocation propagation behaviors. CrystEngComm, 2021, 23, 5039-5044.	1.3	1
138	Modulation of Growth Rate by Electric Current in Liquid-Phase Epitaxy of 4H-SiC. Japanese Journal of Applied Physics, 2013, 52, 085503.	0.8	1
139	New Crucible Design for SiC Single Crystal Growth by Sublimation. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	0
140	Defect Analysis of SiC Sublimation Growth by the In-Situ X-Ray Topography. Materials Science Forum, 2001, 353-356, 295-298.	0.3	0
141	Silicon carbide epitaxial layer growths on Acheson seed crystals from silicon melt. Materials Letters, 2002, 57, 307-314.	1.3	0
142	Defect Characterization of 4H-SiC Bulk Crystals Grown on Micropipe Filled Seed Crystals. Materials Science Forum, 2005, 483-485, 315-318.	0.3	0
143	Etch Pits of 4H-Silicon Carbide Surface Formed Using Chlorine Trifluoride Gas. ECS Transactions, 2010, 28, 81-88.	0.3	0
144	Polarity Inversion of SiC(0001) during the Al Doped PVT Growth. Materials Science Forum, 0, 821-823, 73-76.	0.3	0

#	ARTICLE	IF	CITATIONS
145	Formation of Double Shockley Stacking Faults in Heavily Nitrogen Doped 4H-SiC Crystal with Reduction of Residual Stress around Scratch Damage. Materials Science Forum, 0, 1004, 427-432.	0.3	0
146	Low V_F 4H-SiC N-i-P diodes using newly developed low-resistivity p-type substrates. Japanese Journal of Applied Physics, 2020, 59, SGGD14.	0.8	0
147	Depth Distribution of Defects in SiC PiN Diodes Formed Using Ion Implantation or Epitaxial Growth. Physica Status Solidi (B): Basic Research, 0, , 2100419.	0.7	0